Performance of Field-effect Transistors based on Nb$_x$W$_{1-x}$S$_2$ monolayer

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Figure S1. The electrical conductivities of Nb$_x$W$_{1-x}$S$_2$ film as a function of $x$.

Figure S2. Arrhenius plot for barrier height extraction corresponding to Pd–Nb$_{0.15}$W$_{0.85}$S$_2$ contact